

**AMENDMENTS TO THE CLAIMS:**

The listing of claims will replace all prior versions, and listings of claims in the application:

**LISTING OF CLAIMS:**

1. (Currently amended) An electroluminescent device, comprising a semi-reflecting structure, a reflecting structure, and a plurality of intermediate layers for light generation, wherein said semi-reflecting structure thickness is chosen to cause destructive optical interference of ambient light reflected thereby, and said intermediate layers have thicknesses chosen to create a microcavity for causing constructive optical interference of light generated therein and approximately 360° phase change of transmitted ambient light passing therethrough from said semi-reflecting structure and reflecting off said reflecting structure, such that said transmitted ambient light is subjected to further destructive optical interference within said semi-reflecting structure, wherein the intermediate layers are selected to have a refractive index that increases with wavelength.

2. (Original) The electroluminescent device of claim 1, wherein said intermediate layers include a hole-carrier layer and electron-carrier layer with a light generating region at the interface therebetween.

3. (Currently amended) The electroluminescent device of claim 2, wherein said hole-carrier layer comprises TPD and said electron-carrier layer comprises [[A1Q3]] AlQ3.

4. (Original) The electroluminescent device of claim 3, wherein said intermediate layers include a buffer layer of CuPC adjacent said TPD layer.

5. (Currently amended) The electroluminescent device of claim 4, wherein said intermediate layers include a conductive layer of ITO adjacent said CuPC layers buffer layer.

6. (Currently amended) The electroluminescent device of claim 5, wherein said thicknesses of the intermediate layers are as follows: [[A1Q3]] AlQ3 = 200 to 800 Å, TPD = 200 to 500 Å, CuPC = 0 to 500 Å, ITO = 0 to 2500 Å.

7. (Currently amended) The electroluminescent device of claim 1, wherein said semi-reflecting structure comprises at least one layer of [[A1]] Al, SiO<sub>2</sub> and Cr.

8. (Currently amended) The electroluminescent device of claim 1, wherein said reflecting structure comprises a layer of [[A1]] Al.

9. (Currently amended) The electroluminescent device of any of claims 1 to 8 claim 1, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.

10. (Currently amended) The electroluminescent device of any of claims 1 to 8 claim 1, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.

11. (Original) The electroluminescent device of claim 10, wherein said substrate is one of either clear plastic or glass.

12. (Original) The electroluminescent device of claim 1, wherein said intermediate layers include one of either light emitting polymers or inorganic light emitting materials.

13. (Currently amended) The electroluminescent device of claim 7, wherein said semi-reflecting structure comprises [[A1SiO]] AlSiO (ratio 3:2, 5.5nm), SiO<sub>2</sub> (60nm), and aluminum (10 nm).

14. (Currently amended) The electroluminescent device of claim 6, wherein said thicknesses of the intermediate layers are as follows: [[A1Q3]] AlQ3 = 600 Å, TPD = 450 Å, CuPC = 250 Å, ITO = 1200 Å.

15. (Previously presented) The electroluminescent device of claim 1, wherein said intermediate layers are selected such that the 360° phase change extends over the

visible light range.

16. (Cancelled)

17. (Currently amended) The electroluminescent device of ~~any~~ of claim 7, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.

18. (Currently amended) The electroluminescent device of ~~any~~ of claim 7, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.

19. (Currently amended) The electroluminescent device of ~~any~~ of claim 8, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.

20. (Currently amended) The electroluminescent device of ~~any~~ of claim 8, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.